Package Code

SSMini3-F3 • Pin Name 1: Base

> 2: Emitter 3: Collector

UNR92AVG

Silicon NPN epitaxial planar type

For digital circuits

Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I _C	80	mA	
Total power dissipation	P _T	125	mW	8
Junction temperature	Tj	125	°C	\sim
Storage temperature	T _{stg}	-55 to +125	5°C 7	<u>`</u> .@

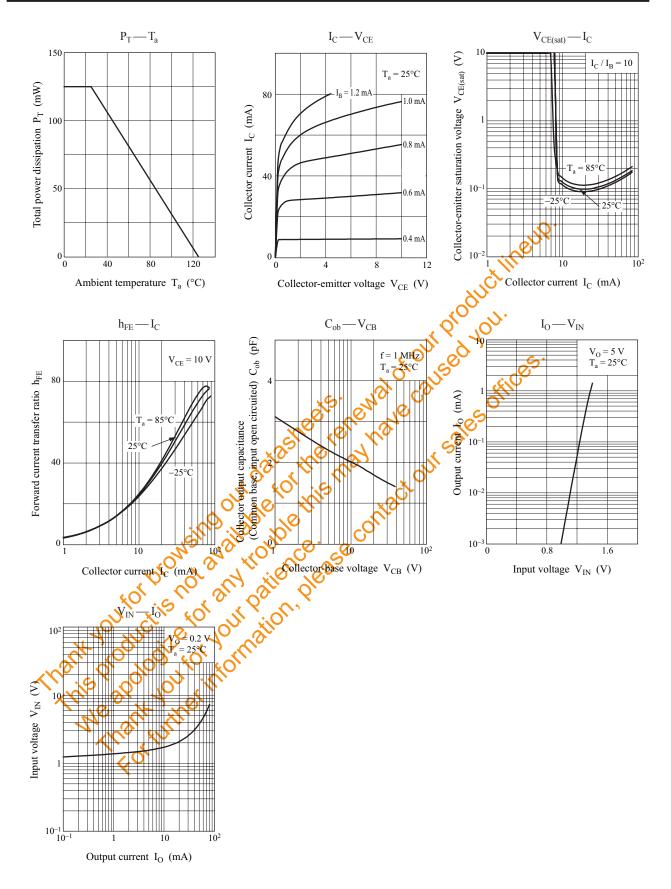
	. ·O·	$\sim \infty$
Electrical Characteristic	25°C±3	× 69

				- C ~			
Collector-base voltage (Emitter open)	V _{CBO}	50	V Ma	rking Syr	nhol· KE	5	
Collector-emitter voltage (Base open)	V _{CEO}	50	V V		•		
Collector current	I _C	80	V MA mW MW	ernalCon	nection		
Total power dissipation	P _T	125	mW KO K	, o	R	.∕⊸c	
Junction temperature	Tj	125	°C 0, 0, 1/2	B o		ί, _α	
Storage temperature	T _{stg}	-55 to +125	S°C NO CO	0	^K ₂	••• E	
NOWSI	availat	outer the	$ \begin{array}{c} V \\ \hline V \\ \hline mA \\ \hline mW \\ \hline oC \\ \hline contact \\ \hline contine \\ \hline conditions \\ $				
Electrical Characteristics T _a	°C±3°C		Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	Усво	$C = 10 \mu$ A	$I_{\rm F} = 0$	50			V
Collector-emitter voltage (Base open)	VCEO	$I_{\rm C} = 2 \rm{mA}$		50			•
			$, I_{\rm B} = 0$	50			V
Collector-base cutoff current Emitter oper	n) Q _{CBO}	$V_{CB} = 50$ V		50		0.1	-
Collector-base cutoff current Emitter oper Collector-emitter cutoff current (Base ope		$V_{\rm CB} = 50$ V	V, $I_E = 0$	50		0.1	V
-	n) I _{CEO}	$V_{\rm CB} = 50$ V	V, $I_E = 0$ V, $I_B = 0$	30			V µA
Collector-emitter cutoff current (Base ope	n) I _{CEO}	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$	V, $I_E = 0$ V, $I_B = 0$	6		0.5	V μΑ μΑ
Collector-eputter cutoff current (Base ope Emitter-base cutoff current (Collector oper	n) I _{CEO} n) I _{EBO}	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$ $V_{CE} = 10 V$	V, $I_E = 0$ V, $I_B = 0$ $I_C = 0$			0.5 2.0	V μΑ μΑ
Collector-epuinter cutoff current (Base ope Emitter-base cutoff current (Collector oper Forward current transfer ratio	n) I _{CEO} n) I _{EBO} h _{FE}	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$ $V_{CE} = 10 V$ $t_{L} = 10 mA$	V, $I_E = 0$ V, $I_B = 0$ $I_C = 0$ V, $I_C = 5 \text{ mA}$			0.5 2.0 20	V μΑ μΑ mA
Collector-epuitter cutoff current (Base ope Emitter-base cutoff current (Collector oper Forward current transfer ratio Collector-emitter saturation Coltage	n) I_{CEO} n) I_{EBO} h_{FE} $V_{CE(sa}$	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$ $V_{CE} = 10 V$ $I_{C} = 10 mA$ $V_{CC} = 5 V$	V, $I_E = 0$ V, $I_B = 0$ $I_C = 0$ V, $I_C = 5 \text{ mA}$ A, $I_B = 1.5 \text{ mA}$	6		0.5 2.0 20	V μA μA mA V
Collector-eputter cutoff current (Base one Emitter-base cutoff current Collector oper Forward current transfer ratio Collector-emitter saturation Voltage Output voltage high-level	n I_{CEO} n I_{EBO} h_{FE} $V_{CE(sa}$ V_{OH}	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$ $V_{CE} = 10 V$ $I_{C} = 10 mA$ $V_{CC} = 5 V$	V, $I_E = 0$ V, $I_B = 0$ I _C = 0 V, $I_C = 5 \text{ mA}$ A, $I_B = 1.5 \text{ mA}$ V B = 0.5 V, $R_L = 1 \text{ k}\Omega$	6	2.2	0.5 2.0 20 0.25	V μA mA V V
Collector-emitter cutoff current (Base ope Emitter-base cutoff current (Collector oper Forward current transfer ratio Collector-emitter saturation Voltage Output voltage high-level Output voltage low-level	n I_{CEO} n I_{EBO} h_{FE} $V_{CE(sa}$ V_{OH}	$V_{CB} = 50 V$ $V_{CE} = 50 V$ $V_{EB} = 6 V$ $V_{CE} = 10 V$ $V_{CC} = 5 V$ $V_{CC} = 5 V$	V, $I_E = 0$ V, $I_B = 0$ I _C = 0 V, $I_C = 5 \text{ mA}$ A, $I_B = 1.5 \text{ mA}$ V B = 0.5 V, $R_L = 1 \text{ k}\Omega$	6	2.2	0.5 2.0 20 0.25 0.2	V μA μA mA V V V V V

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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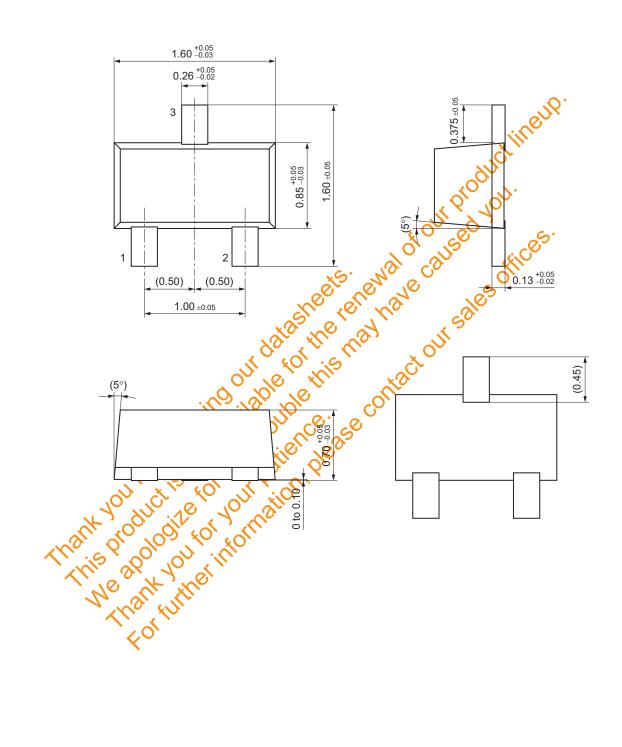
Panasonic



Panasonic

SSMini3-F3

Unit: mm



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